

Minimizing Degradation of SiC Bipolar Semiconductor Devices

ABSTRACT OF THE DISCLOSURE

A bipolar device has at least one p-type layer of single crystal silicon carbide and at
5 least one n-type layer of single crystal silicon carbide, wherein those portions of those
stacking faults that grow under forward operation are segregated from at least one of the
interfaces between the active region and the remainder of the device.

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